WSD30L88DN56

Dual P-Channel MOSFET

General Description

The WSD30L88DN56 is the highest performance trench Dual P-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD30L88DN56 meet the RoHS and Green Product requirement 100% E_{AS} guaranteed with full function reliability approved.

Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
-30V	11.5mΩ	-49A

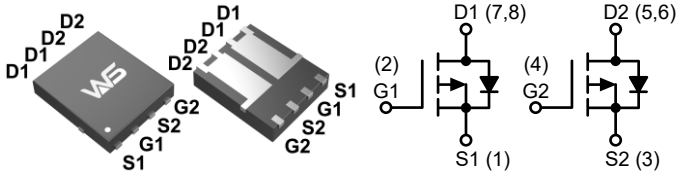
Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ -10V [1]	-49	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ -10V [1]	-23	
I_{DM}	Pulsed Drain Current [2]	-120	
E_{AS}	Single Pulse Avalanche Energy [3]	68	mJ
P_D@T_C=25°C	Total Power Dissipation [4]	40	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction-Ambient [1]	---	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-Case [1]	---	2.4	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250μA	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C, I_D=-1mA	---	-0.0332	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance [2]	V_{GS}=-10V , I_D=-10A	---	11.5	16	mΩ
		V_{GS}=-4.5V , I_D=-5A	---	16	20	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=-250μA	-1.2	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.4	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25°C	---	---	1.0	μA
		V_{DS}=-24V , V_{GS}=0V , T_J=55°C	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
g_{fs}	Forward Transconductance	V_{DS}=-5V , I_D=-10A	35	---	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f = 1.0MHz	---	7	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-10V , I_D=-5A	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	5.5	---	
Q_{gd}	Gate-Drain Charge		---	5.9	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GEN}=-10V , R_G=3Ω , I_D=-1A	---	9	---	ns
T_r	Rise Time		---	13	---	
$T_{d(off)}$	Turn-Off Delay Time		---	48	---	
T_f	Fall Time		---	20	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f = 1.0MHz	---	2135	---	pF
C_{oss}	Output Capacitance		---	282	---	
C_{rss}	Reverse Transfer Capacitance		---	255	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current [1,6]	V_G=V_D=0V , Force Current	---	---	-29.5	A
I_{SM}	Pulsed Source Current [2,6]		---	---	-44	
V_{SD}	Diode Forward Voltage [2]	V_{GS}=0V , I_S=-1A , T_J=25°C	---	---	-1.2	V

Note:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper, t < 10sec.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating . The test condition is V_{DD}=-15V, V_{GS}=-10V, L=0.1mH, I_{AS}=-36A
4. The power dissipation is limited by 150°C junction temperature.
5. The Min. value is 100% E_{AS} tested guarantee.
6. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

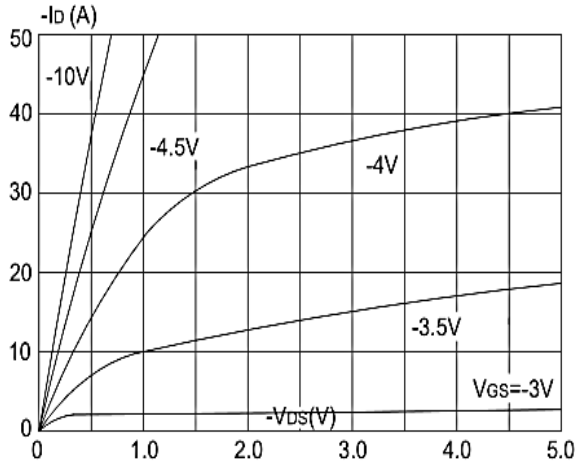


Figure1: Output Characteristics Figure

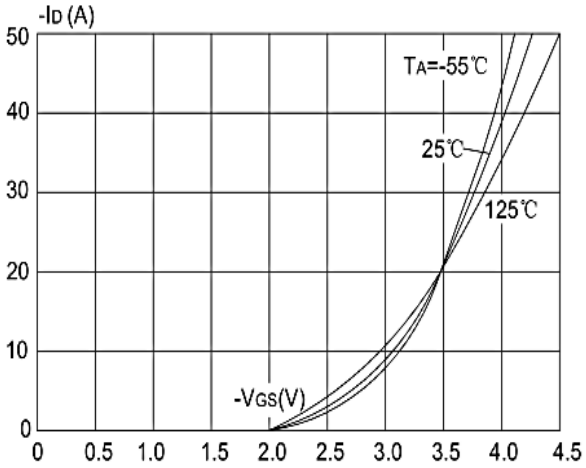


Figure2: Typical Transfer Characteristics

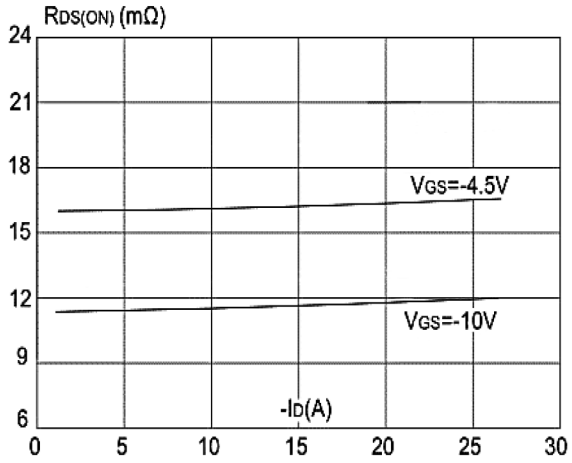


Figure 3:On-resistance vs. Drain Current

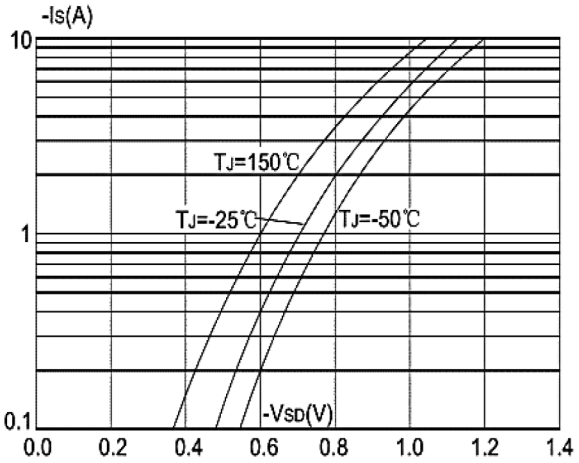


Figure 4: Body Diode Characteristics

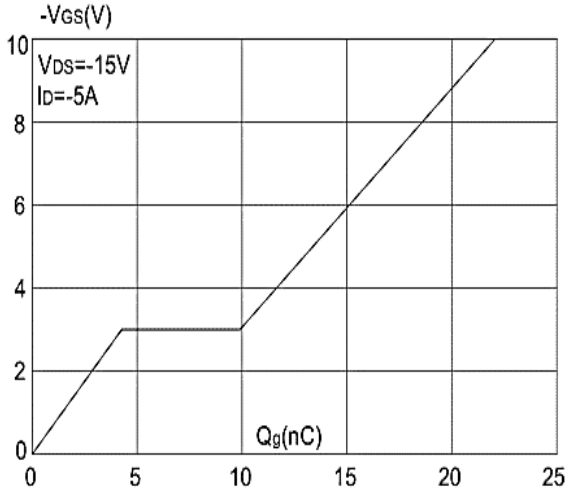


Figure 5: Gate Charge Characteristics

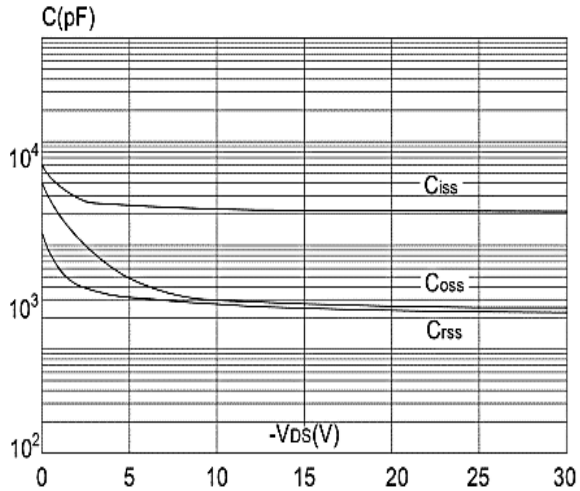


Figure 6: Capacitance Characteristics

Typical Characteristics (Cont.)

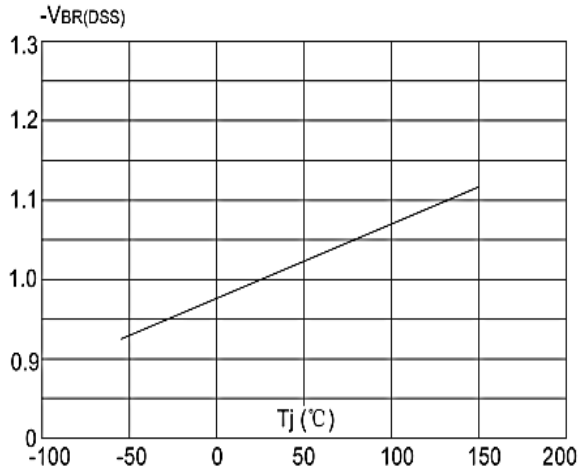


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

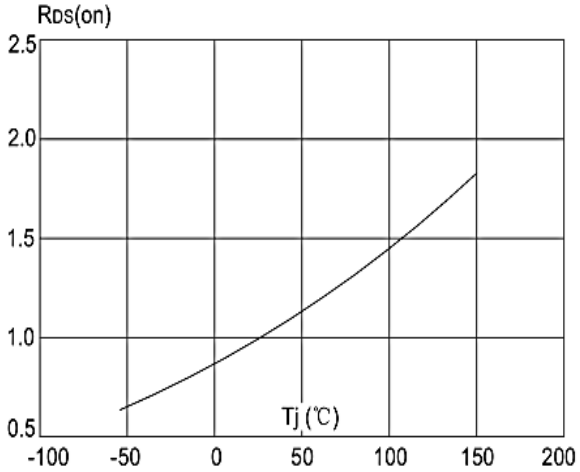


Figure 8: Normalized on Resistance vs. Junction Temperature

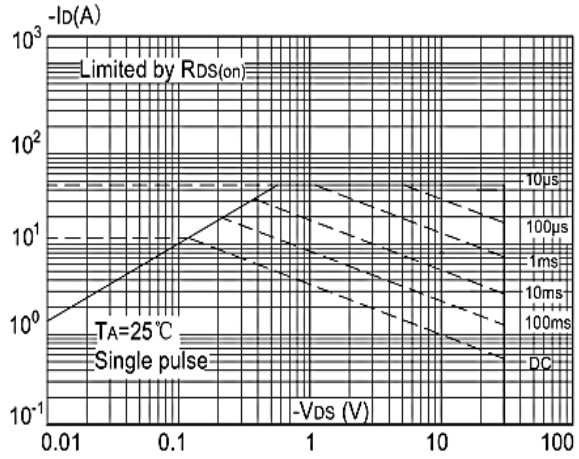


Figure 9: Maximum Safe Operating Area

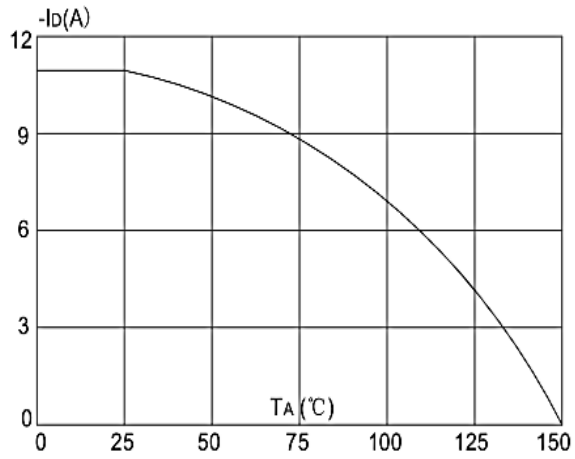


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

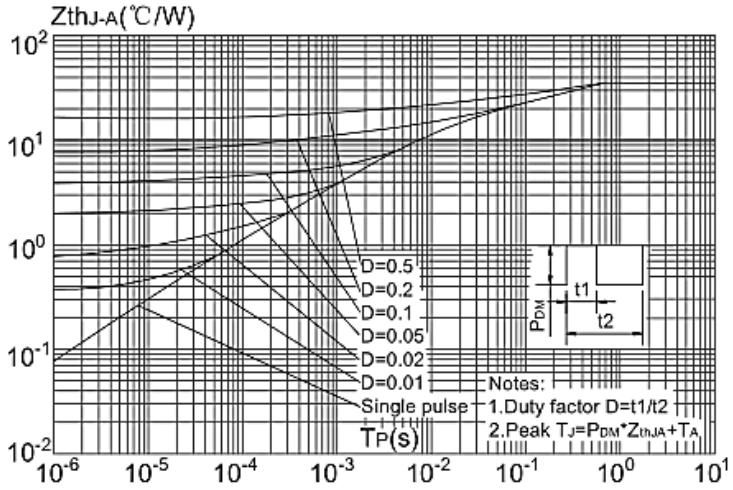
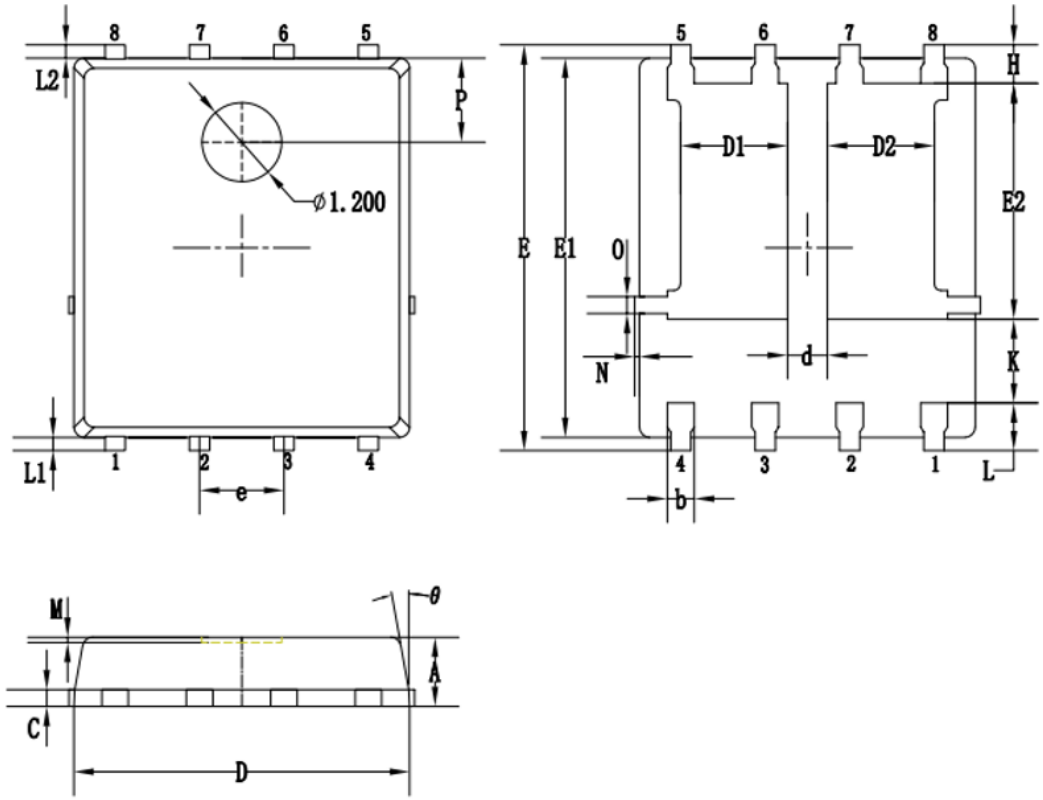


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Packaging information



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.61	1.71
d	0.50	0.60	0.70
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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